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# Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- · Logic-level compatible
- · Very fast switching
- · Enhanced power dissipation capability of 1.4 W
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

## 3. Applications

- · Relay driver
- · High-speed line driver
- · High-side loadswitch
- · Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-30	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-4.4	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -10 V; $I_D$ = -3.3 A; $T_j$ = 25 °C		-	60	80	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# **5. Pinning information**

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D
2	D	drain		
3	G	gate	<u>0</u> <u>1 1 2 13</u>	G $\downarrow$ $\downarrow$ $\downarrow$
4	S	source	TSOP6 (SOT457)	
5	D	drain		
6	D	drain		S 017aaa259

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PMN70EPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

# 7. Marking

#### **Table 4. Marking codes**

Type number	Marking code
PMN70EPE	G2

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-4.4	Α
		V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[1]	-	-3.3	Α
		V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C	[1]	-	-2.1	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-14	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	570	mW
			[1]	-	1.4	W
		T <sub>sp</sub> = 25 °C		-	6.25	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain d	iode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.4	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

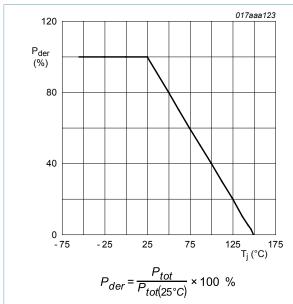


Fig. 1. Normalized total power dissipation as a function of junction temperature

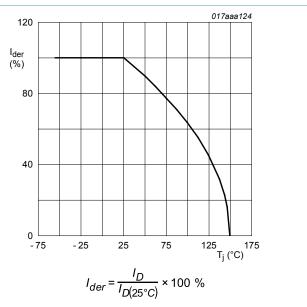
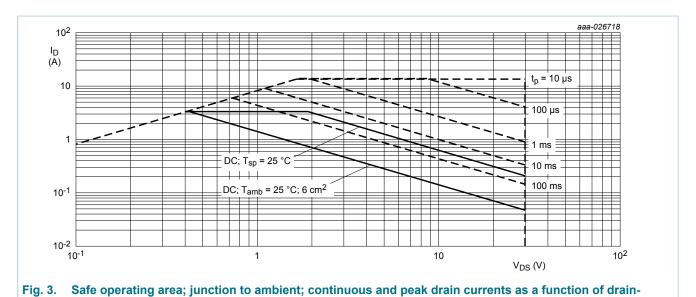


Fig. 2. Normalized continuous drain current as a function of junction temperature

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# source voltage

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance		[1]	-	190	220	K/W
	from junction to ambient		[2]	-	78	90	K/W
		in free air; t ≤ 5 s	[2]	-	47	54	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	15	20	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

#### 30 V, P-channel Trench MOSFET

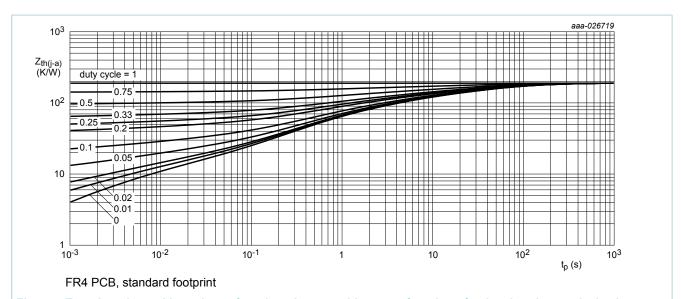


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

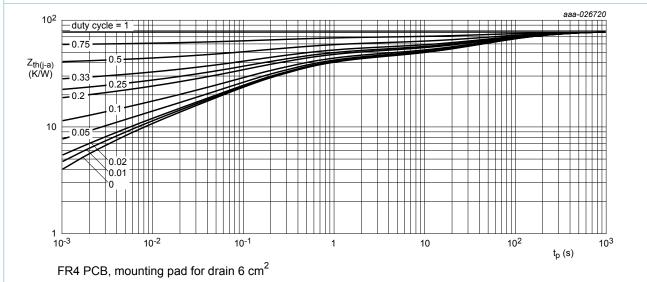


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$	-30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$	-1	-2	-3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	10	μΑ
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-100	nA
200	drain-source on-state	$V_{GS}$ = -10 V; $I_D$ = -3.3 A; $T_j$ = 25 °C	-	60	80	mΩ
	resistance	V <sub>GS</sub> = -10 V; I <sub>D</sub> = -3.3 A; T <sub>j</sub> = 150 °C	-	91	121	mΩ
		$V_{GS} = -4.5 \text{ V}; I_D = -2.6 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	96	140	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -2 A; $T_j$ = 25 °C	-	12.6	-	S
$R_G$	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	12	-	Ω
Dynamic cl	naracteristics					
Q <sub>G(tot)</sub>	$V_{DS} = -15 \text{ V}; I_D = -3.3 \text{ A}; V_{GS} = -10 \text{ V};$		-	6.5	11.5	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	1.2	-	nC
$Q_{GD}$	gate-drain charge		-	1.2	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	370	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	64	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	44	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -15 V; $I_D$ = -3.3 A; $V_{GS}$ = -10 V;	-	5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	8	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	19	-	ns
f	fall time		-	7.5	-	ns
Source-dra	in diode		'	,	,	,
$V_{SD}$	source-drain voltage	$I_S = -1.4 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_i = 25 ^{\circ}\text{C}$	_	-0.8	-1.2	V

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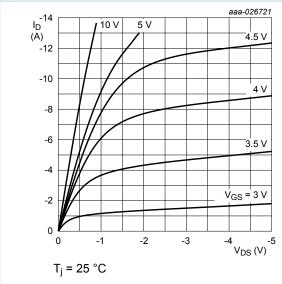


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

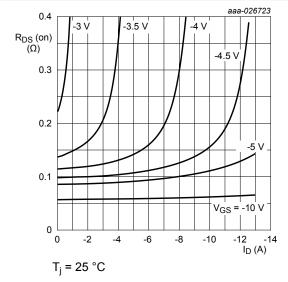


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

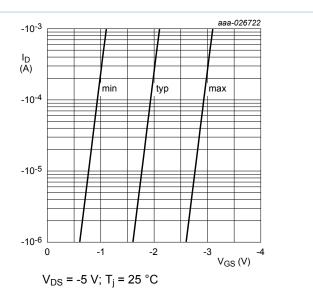


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

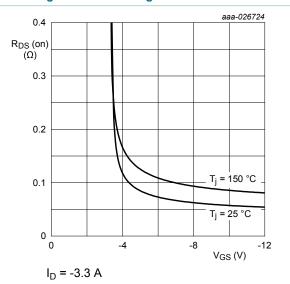


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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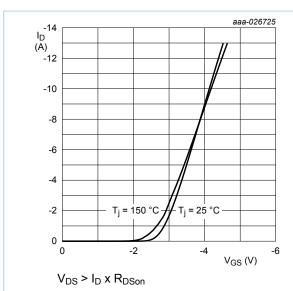


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

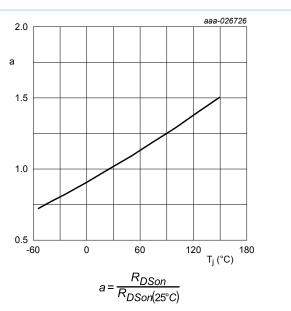


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

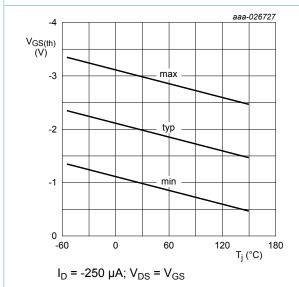


Fig. 12. Gate-source threshold voltage as a function of junction temperature

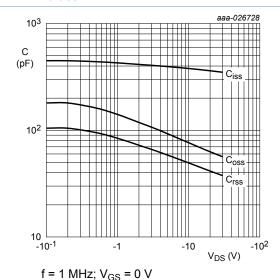


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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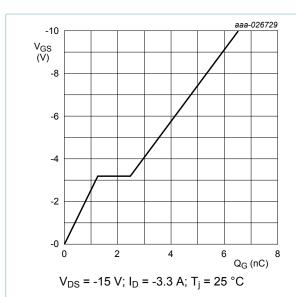


Fig. 14. Gate-source voltage as a function of gate charge; typical values

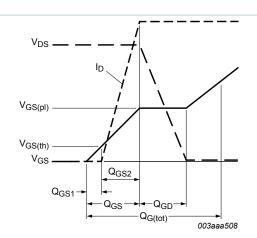


Fig. 15. Gate charge waveform definitions

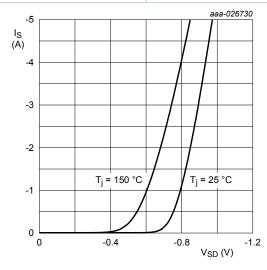
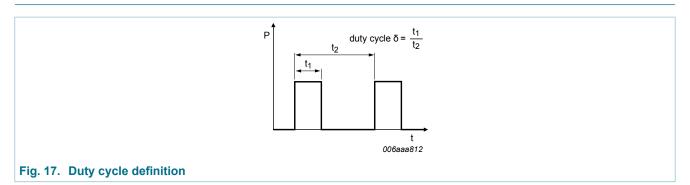


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



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# 12. Package outline

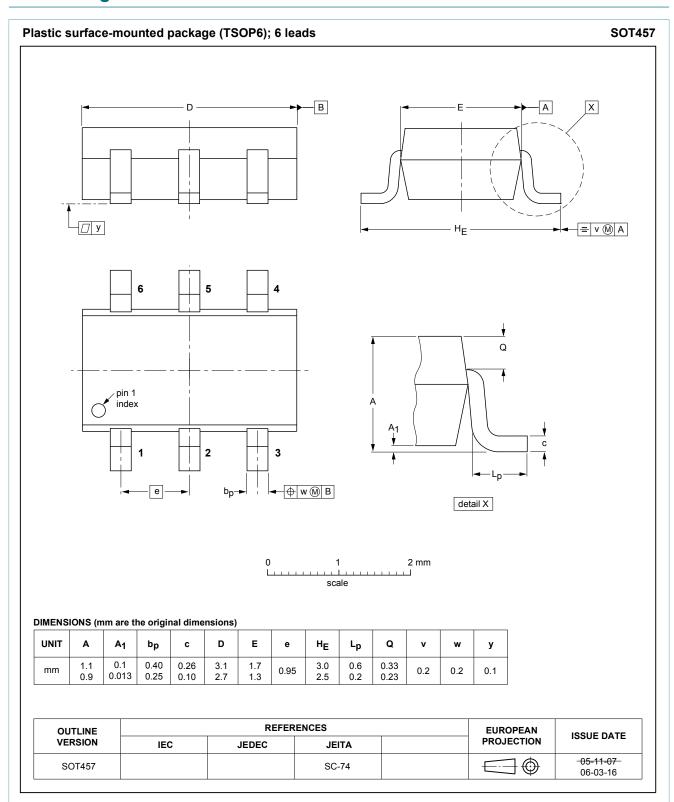
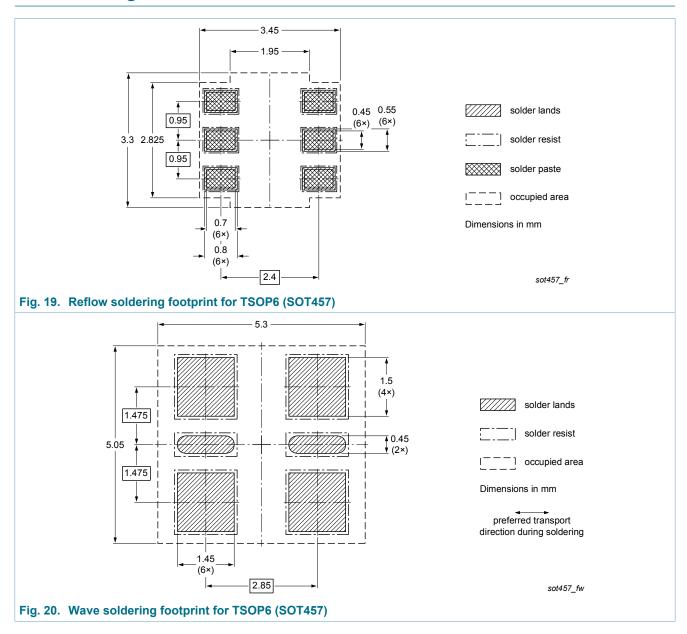


Fig. 18. Package outline TSOP6 (SOT457)

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## 13. Soldering



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# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN70EPE v.1	20170523	Product data sheet	-	-

#### 30 V, P-channel Trench MOSFET

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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